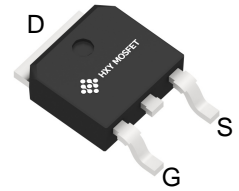




## General Description

The IPD35N10S3L26ATMA1 use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics. This device is specially designed to get better ruggedness.



TO-252-2L

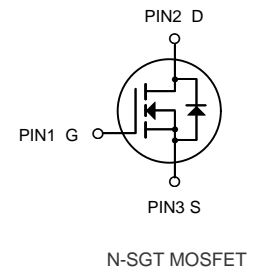
## General Features

$V_{DS} = 100V$   $I_D = 40A$

$R_{DS(ON)} < 23m\Omega$  @  $V_{GS} = 10V$

## Applications

- Consumer electronic power supply
- Motor control
- Synchronous-rectification
- Isolated DC
- Synchronous-rectification applications



## Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IPD35N10S3L26ATMA1	TO-252-2L	HXY MOSFET	2500

## Absolute Maximum Ratings at $T_j = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Unit
VDS	Drain source voltage	100	V
VGS	Gate source voltage	$\pm 20$	V
ID	Continuous drain current , $T_C = 25^\circ C$	40	A
ID, pulse	Pulsed drain current , $T_C = 25^\circ C$	100	A
$P_D$	Power dissipation , $T_C = 25^\circ C$	27	W
EAS	Single pulsed avalanche energy	16	mJ
Tstg, Tj	Operation and storage temperature	-55 to 150	$^\circ C$
R $\theta$ JC	Thermal resistance, junction-case	4.65	$^\circ C/W$
R $\theta$ JA	Thermal resistance, junction-ambient	62	$^\circ C/W$



**Electrical Characteristics** at  $T_j=25\text{ }^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	100	-	-	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS} = 80V, V_{GS} = 0V$	-	-	1	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2	1.8	2.6	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 15A$	-	20	23	m $\Omega$
		$V_{GS} = 4.5V, I_D = 10A$	-	-	33	m $\Omega$
$g_{fs}$	Forward Threshold Voltage	$V_{DS} = 10V, I_D = 20A$	-	22	-	S
$R_g$	Gate Resistance	$V_{DS} = V_{GS} = 0V, f = 1.0MHz$	-	1.62	-	$\Omega$
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = 50V, V_{GS} = 0V,$ $f = 1.0MHz$	-	822	-	pF
$C_{oss}$	Output Capacitance		-	310	-	pF
$C_{riss}$	Reverse Transfer Capacitance		-	23.5	-	pF
<b>Switching Characteristics</b>						
$Q_g$	Total Gate Charge	$V_{DS} = 50V, I_D = 20A,$ $V_{GS} = 10V$	-	22.7	-	nC
$Q_{gs}$	Gate-Source Charge		-	6.2	-	
$Q_{gd}$	Gate-Drain("Miller") Charge		-	5.3	-	
$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = 50V, I_D = 20A,$ $R_G = 3\Omega, V_{GS} = 10V$	-	15	-	ns
$t_r$	Turn-On Rise Time		-	3.2	-	
$t_{d(off)}$	Turn-Off Delay Time		-	30	-	
$t_f$	Turn-Off Fall Time		-	7.6	-	
<b>Diode Characteristics</b>						
$I_S$	Continuous Source Current		-	-	40	A
$V_{SD}$	Diode Forward Voltage	$I_S = 20A, V_{GS} = 0V$	-	0.88	1.0	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 20A,$	-	45	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di_{SD}/dt = 100A/\mu s$	-	59	-	nC

Notes:

1. The value of  $R_{\theta JC}$  is measured in a still air environment with  $T_A = 25^\circ C$  and the maximum allowed junction temperature of  $150^\circ C$ . The value in any given application depends on the user's specific board design.
2. The power dissipation  $P_D$  is based on  $T_{J(MAX)} = 150^\circ C$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
3. Single pulse width limited by junction temperature  $T_{J(MAX)} = 150^\circ C$ .
4. The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to case  $R_{\theta JC}$  and case to ambient.
5. The maximum current rating is package limited.
6. The EAS data shows Max. rating. The test condition is  $V_{DS} = 50V, V_{GS} = 10V, L = 0.5mH$



## Electrical Characteristics Diagrams

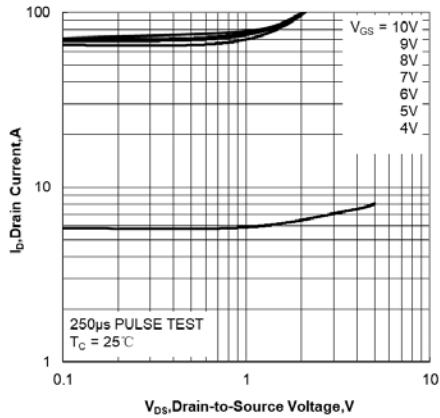


Figure 1. Output Characteristics

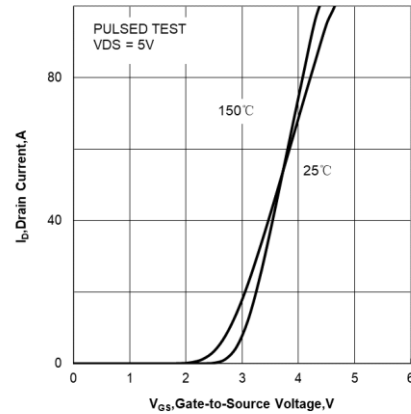


Figure 2. Transfer Characteristics

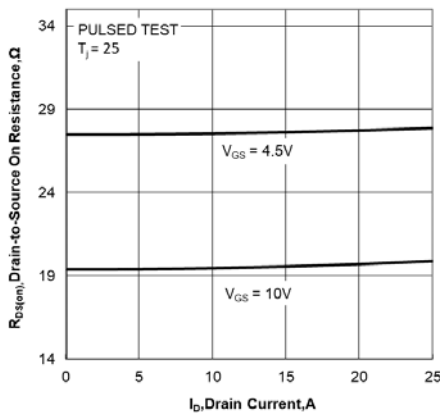


Figure 3. Drain-to-Source On Resistance vs Drain Current

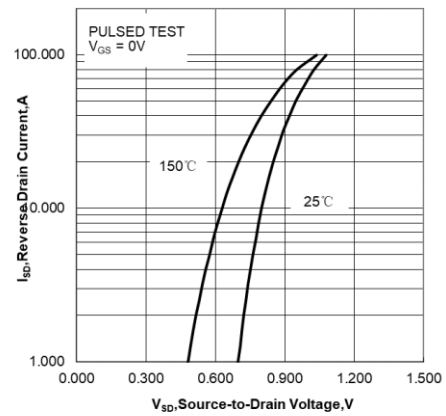


Figure 4. Body Diode Forward Voltage vs Source Current and Temperature

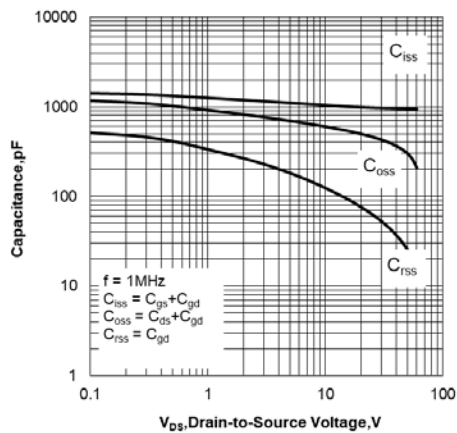


Figure 5. Capacitance Characteristics

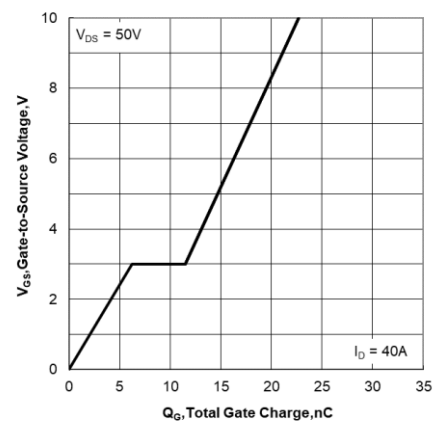


Figure 6. Gate Charge Characteristics

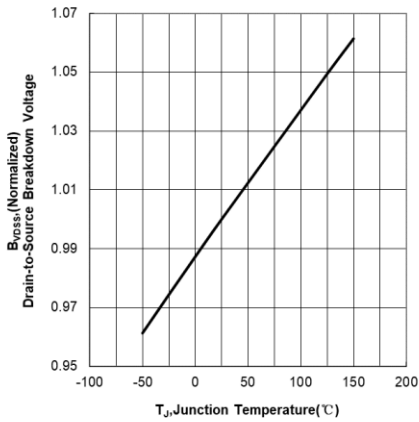


Figure 7. Normalized Breakdown Voltage vs Junction Temperature

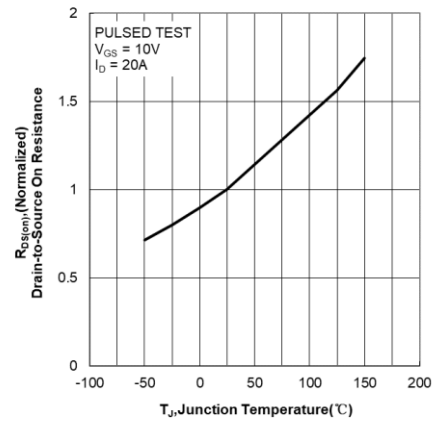


Figure 8. Normalized On Resistance vs Junction Temperature

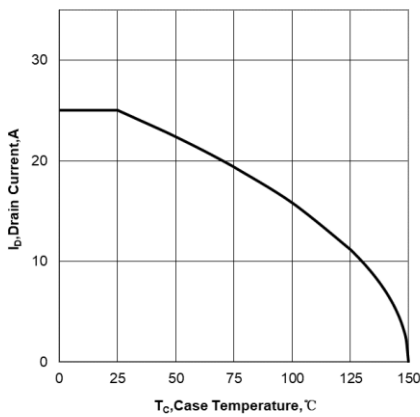


Figure 9. Maximum Continuous Drain Current vs Case Temperature

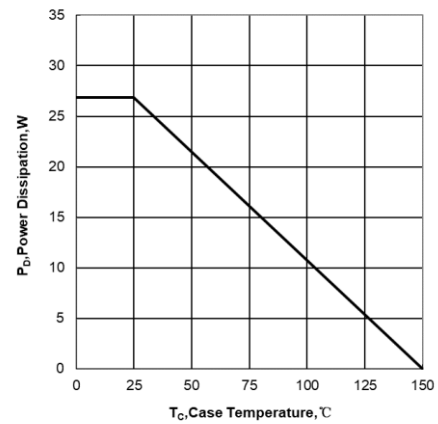


Figure 10. Maximum Power Dissipation vs Case Temperature

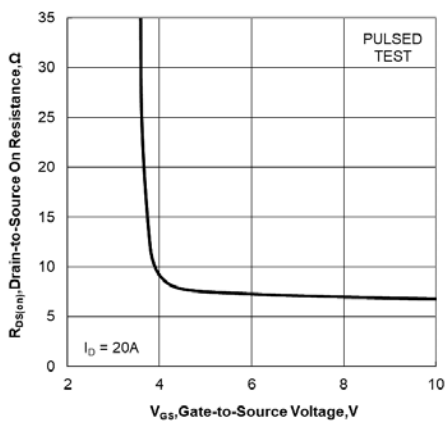


Figure 11. Drain-to-Source On Resistance vs Gate

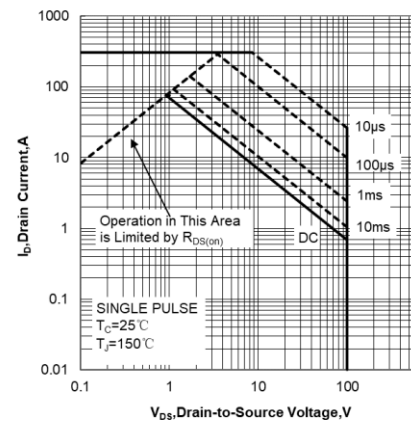


Figure 12. Maximum Safe Operating Area

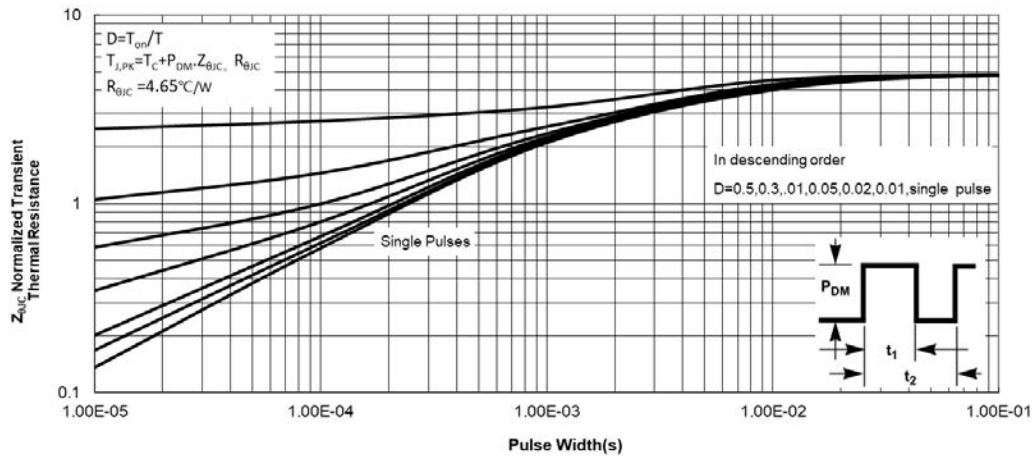
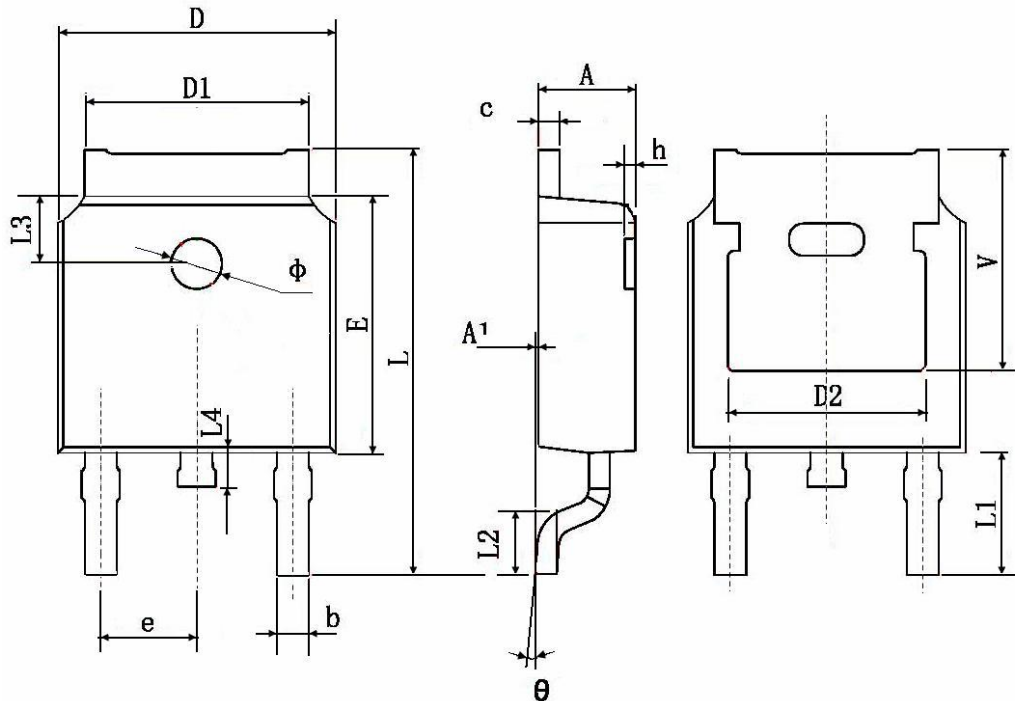


Figure 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case



**TO-252-2L Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
phi	1.100	1.300	0.043	0.051
theta	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



### Attention

- Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.
- HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.
- Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.